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TITLE

LIGHT EMITTING ELEMENT AND

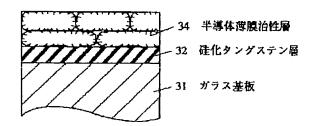
DISPLAY ELEMENT, AND

MANUFACTURE OF THE SAME

31

硅化タングステン層 ガラス基板

(b)



ABSTRACT :

PROBLEM TO BE SOLVED: To provide a light emitting element and a display element which can be manufactured in a safe and inexpensive process by making it unnecessary to contain any harmful material as a complete material and element and to provide a method for manufacturing the light emitting element and the display element.

SOLUTION: A micro crystalline thin film whose Argon(Ar) gas pressure is 5 mTorr and whose mean particle diameter is about 10 nm is accumulated by 300 nm so that an accumulated semiconductor thin film 33 can be obtained. The grain diameter of the accumulated semiconductor thin film 33 of micro crystallines is made large just after the accumulation, and short time radiation annealing is carried out so that surface lattice re-array can be promoted and non-radiation re-connection center based on a surface specific defective level can be reduced. An Xenon chloride(Xe CI) excimer laser having wavelength which can be preferentially absorbed by the accumulated semiconductor thin film 33 and largely reflected on a siliceous tungsten layer 32 is adopted as an excitation light so that a heat load on a glass substrate can be reduced.

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